

ZERO BIAS SCHOTTKY DIODE

DESCRIPTION:

The **ASI 3486** is a Silicon Schottky Barrier Diode Designed for High Sensitivity Zero Bias Detector Applications up to 10 GHz.

FEATURES INCLUDE:

- Replacement for **HSCH3486** and **MA4E928** series
- -56 dBm T_{SS} Typical @ 10 GHz
- Hermetic Glass Package

MAXIMUM RATINGS

I_F	10 mA
V_R	2.0 V
P_{DISS}	300 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+150^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
$T_{soldering}$	$+230^\circ C$ for 5 Seconds

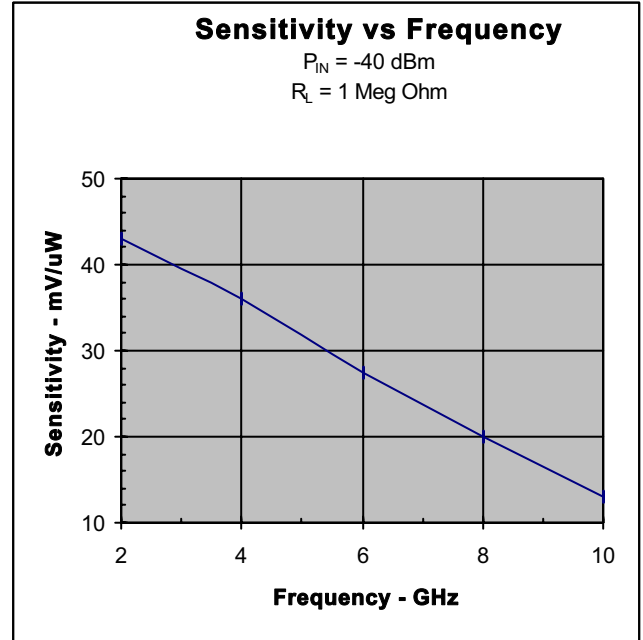
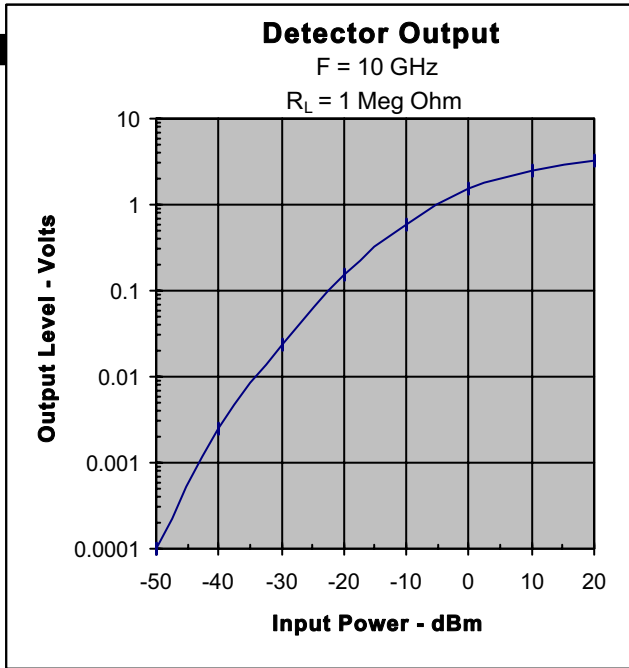


CHARACTERISTICS $T_C = 25^\circ C$

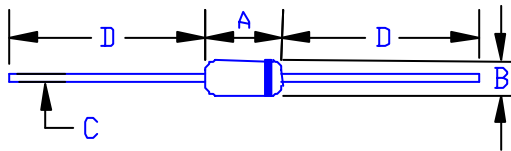
SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_F	$I_F = 1.0$ mA			185	225	mV
V_{BR}	$I_R = 200$ μA		0.8			V
C_{T0}	$V_R = 0$ V	$f = 1.0$ MHz		0.4		pF
T_{SS}	$B_W = 2.0$ MHz	$f = 10$ GHz	-54			dBm
γ	$P_{IN} = -40$ dBm	$f = 10$ GHz	7.5			mV/ μW
R_v	$P_{IN} = -40$ dBm	$f = 10$ GHz	2.0		8.0	K Ohms

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DYNAMIC CHARACTERISTICS



PACKAGE OUTLINE



Body Color: Clear

STYLE 01		
	MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.150/3.81	.170/4.318
B	.068/1.727	.076/1.930
C	.014/.356	.020/.508
D	1.00/25.4	
E	CP=.027pF	
F	Lp=2.5nH	
G		

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